

TO-92 Plastic-Encapsulate Transistors

2SB561 TRANSISTOR (PNP)

FEATURES

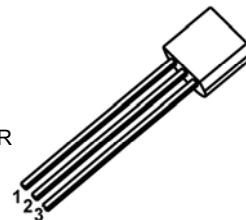
- Low Frequency Power Amplifier

MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-20	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current	-700	mA
P_C	Collector Power Dissipation	500	mW
$R_{\theta JA}$	Thermal Resistance From Junction To Ambient	250	$^{\circ}\text{C}/\text{W}$
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

TO - 92

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-0.01\text{mA}, I_E=0$	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1\text{mA}, I_B=0$	-20			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-0.01\text{mA}, I_C=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB}=-20\text{V}, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5\text{V}, I_C=0$			-1	μA
DC current gain	h_{FE}^*	$V_{CE}=-1\text{V}, I_C=-0.15\text{A}$	85		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-0.5\text{A}, I_B=-0.05\text{A}$			-0.5	V
Base-emitter voltage	V_{BE}	$V_{CE}=-1\text{V}, I_C=-0.15\text{A}$			-1	V
Collector output capacitance	C_{ob}	$V_{CB}=-10\text{V}, I_E=0, f=1\text{MHz}$		20		pF
Transition frequency	f_T	$V_{CE}=-1\text{V}, I_C=-0.15\text{A}$		350		MHz

*Pulse test

CLASSIFICATION OF h_{FE}

RANK	B	C
RANGE	85-170	120-240